

ABSTRACT OF THE DISCLOSURE

According to a method for impurity implantation, a substrate is positioned on a table provided within a chamber in which a vacuum will be introduced and also an
5 implantation impurity is supplied. A first high frequency electric power is applied to a plasma generating element to thereby cause a plasma so that the impurity in the chamber is implanted in the substrate. Also, a second high
10 frequency electric power is applied to the table. Detected are a condition of the plasma in the chamber and a voltage or current in the table. Controller controls at least one of the first and second high frequency electric power according to the detected condition of the plasma and/or
15 the detected voltage or current, thereby controlling an implantation concentration of the impurity to be implanted.